

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

1 - 26. (Canceled)

1 27. (New): An electronic device comprising a semiconductor device provided
2 with pads and a substrate provided with pads on which said semiconductor device is mounted,
3 said pads of said semiconductor device being bonded to said pads of said substrate through
4 junctions each including Cu balls formed by one or a mixture of an elemental Cu, a Cu alloy, and
5 a Cu-containing compound, and by a Cu-Sn compound containing Cu_6Sn_5 , said Cu balls being
6 bonded to each other by said Cu_6Sn_5 .

1 28. (New): An electronic device according to claim 27, wherein said Cu-Sn
2 compound further includes Cu_3Sn .

1 29. (New): An electronic device according to claim 28, wherein said Cu_3Sn is
2 disposed in a region between said Cu-balls and said Cu_6Sn_5 .

1 30. (New): An electronic device according to claim 27, wherein said Cu_6Sn_5
2 has a thickness of about a few micrometers.

1 31. (New): An electronic device according to claim 27, wherein said Cu_6Sn_5
2 is formed by reflowing said Cu-balls and Sn-base solder at a temperature higher than a melting
3 point of said Sn-base solder and lower than a melting point of said Cu-balls.

1 32. (New): An electronic device according to claim 31, wherein said Sn-base
2 solder comprises eutectic Sn-Cu solder, eutectic Sn-Cu solder to which at least one of In, Zn and
3 Bi is added, eutectic Sn-Ag solder, eutectic Sn-Ag solder to which at least one of In, Zn and Bi is

4 added, eutectic Sn-Ag-Cu solder, or eutectic Sn-Ag-Cu solder to which at least one of In, Zn and
5 Bi is added.

1 33. (New): An electronic device according to claim 31, wherein said Cu-balls
2 have a diameter greater than 5 micrometers.

1 34. (New): An electronic device comprising a semiconductor device provided
2 with pads and a substrate provided with pads on which said semiconductor device is mounted,
3 said pads of said semiconductor device being bonded to said pads of said substrate by way of
4 junctions, each junction including Cu balls comprising one or a mixture of elemental Cu, a Cu
5 alloy, and a Cu compound, said Cu balls further comprising a Cu-Sn compound containing
6 Cu_6Sn_5 and Cu_3Sn , said Cu_3Sn being formed at peripheries of said Cu balls.

1 35. (New): An electronic device according to claim 34, wherein said Cu-Sn
2 compound is formed by reflowing said Cu-balls and Sn-base solder at a temperature higher than
3 a melting point of said Sn-base solder and lower than a melting point of said Cu-balls.

1 36. (New): An electronic device according to claim 35, wherein said Sn-base
2 solder comprises eutectic Sn-Cu solder, eutectic Sn-Cu solder to which In, Zn or Bi is added,
3 eutectic Sn-Ag solder, eutectic Sn-Ag solder to which In, Zn or Bi is added, eutectic Sn-Ag-Cu
4 solder or eutectic Sn-Ag-Cu solder to which In, Zn or Bi is added.

1 37. (New): An electronic device according to claim 35, wherein said Cu-balls
2 have a diameter greater than 5 micrometers.